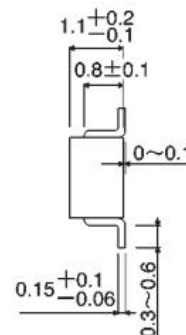
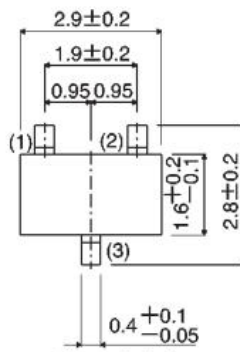


SOT-23-3L Bipolar Transistor 双极型三极管

■ Features 特点

PNP General Purpose 通用

- 1、Emitter
- 2、Base
- 3、Collector



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-80	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-80	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-500	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	200	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	625	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

■ Device Marking 产品打标

H_{FE} (1)	180-390 (R)
Mark	AKR

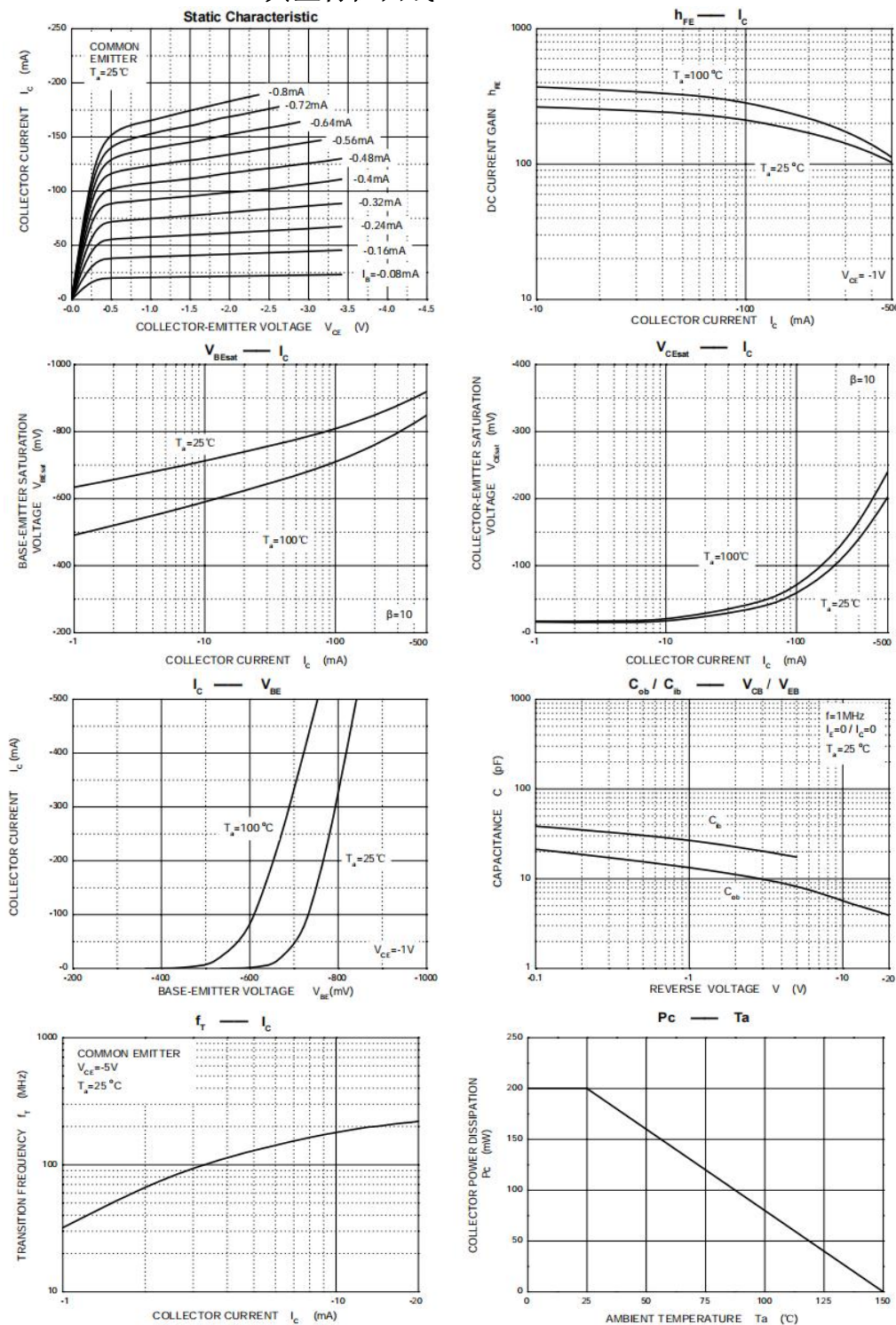
■Electrical Characteristics 电特性

(TA=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(IC= -100μA, IE=0)	BV _{CBO}	-80	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(IC= -10mA, IB=0)	BV _{CEO}	-80	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(IE= -100μA, IC=0)	BV _{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = -80V, IE=0)	I _{CBO}	—	—	-0.1	μA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = -5V, IC=0)	I _{EBO}	—	—	-0.1	μA
DC Current Gain 直流电流增益 (V _{CE} = -3V, IC= -100mA)	H _{FE} (1)	180	—	390	
DC Current Gain 直流电流增益 (V _{CE} = -3V, IC= -500mA)	H _{FE} (2)	45	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 (IC= -500mA, IB= -50mA)	V _{CE(sat)}	—	—	-0.5	V
Base-Emitter On Voltage 基极发射极导通压降 (V _{CE} = -3V, IC= -500mA)	V _{BE}	—	—	-1	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 (IC= -500mA, IB= -50mA)	V _{BE(sat)}	—	—	-1	V
Transition Frequency 特征频率 (V _{CE} = -6V, IC= -20mA)	f _T	—	120	—	MHz
Output Capacitance 输出电容 (V _{CB} = -6V, IE=0, f=1MHz)	C _{ob}	—	13	—	pF

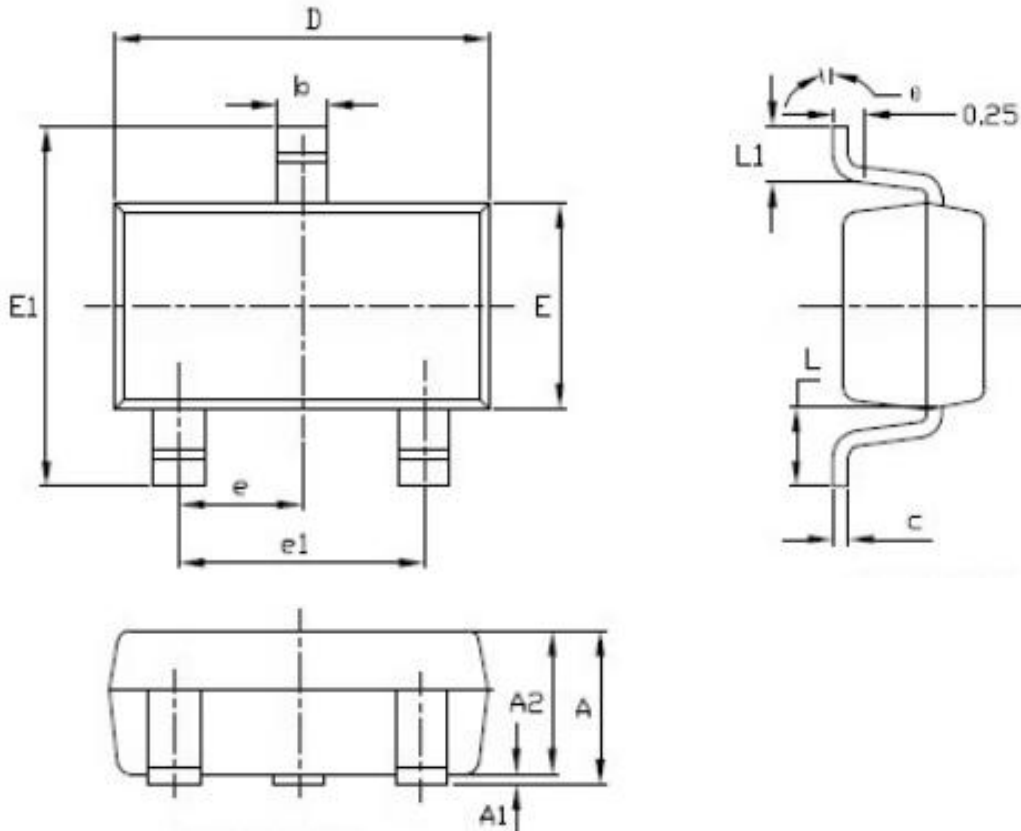
2SB1198R

■ Typical Characteristic Curve 典型特性曲线



2SB1198R

■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.600REF		0.024REF	
L1	0.300	0.600	0.012	0.024



安徽富信半导体科技有限公司
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

θ	0°	8°	0°	8°
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